

A METHOD FOR PROGRAMMING A RESISTIVE MEMORY CELL, A
METHOD AND A MEMORY APPARATUS FOR PROGRAMMING ONE OR
MORE RESISTIVE MEMORY CELLS IN A MEMORY ARRAY

ABSTRACT

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A method for programming a resistive memory cell is provided. The method may include providing a programming signal to the resistive memory cell. The programming signal may include an electrical pulse and a bias pulse coupled with the electrical pulse. The electrical pulse includes an electrical pulse portion, and the bias pulse includes at least two bias pulse portions, wherein the electrical pulse portion is positioned between the at least two bias pulse portions. The bias pulse includes a voltage below a threshold switching voltage of the resistive memory cell. The programming signal includes a peak voltage above the threshold switching voltage of the resistive memory cell.

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Figure 9